

isc Silicon NPN Power Transistor

2SD73

DESCRIPTION

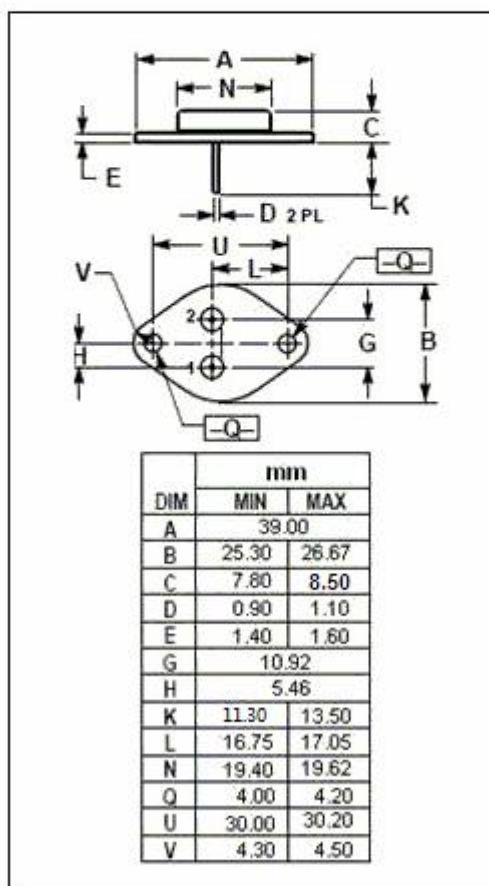
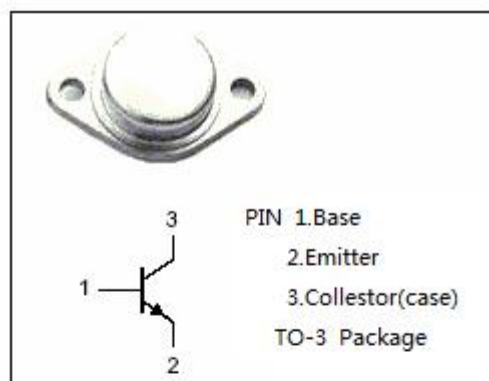
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 100V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
T_J	Junction Temperature	175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~175	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD73****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 30\text{mA}; I_B = 0$	100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}; I_E = 0$	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}; I_C = 0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 0.5\text{A}$			2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C = 1\text{A}; V_{CE} = 5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 100\text{V}; I_E = 0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5\text{V}; I_C = 0$			100	μA
h_{FE-1}	DC Current Gain	$I_C = 1\text{A}; V_{CE} = 5\text{V}$	60		200	
h_{FE-2}	DC Current Gain	$I_C = 4\text{A}; V_{CE} = 5\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = 1\text{A}; V_{CE} = 5\text{V}$		20		MHz